600mA CMOS Linear Regulator

General Description

The EMP8021 low-dropout (LDO) CMOS linear regulators feature low output voltage noise ($63\mu V$), low quiescent current ($50\mu A$), and fast transient response. It guarantees delivery of 600mA output current, and supports preset output voltages ranging from 0.8V to 4.75V with 0.05V increment.

The EMP8021 is ideal for battery-powered applications by virtue of its low quiescent current consumption and its 1nA shutdown mode of logical operation. The regulator provides fast turn-on and start-up time by using dedicated circuitry to pre-charge an optional external bypass capacitor. This bypass capacitor is used to reduce the output voltage noise without adversely affecting the load transient response. The regulator is stable with small ceramic capacitive loads (2.2µF typical).

Additional features include bandgap voltage reference, constant current limiting and thermal overload protection. The EMP8021 is available in miniature SOT-23-5, SC-70-5 and SOT-89-3 package.

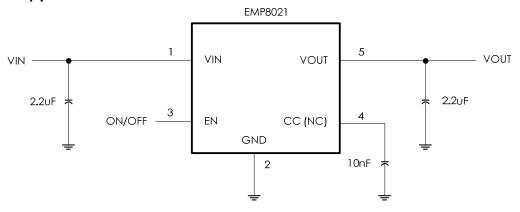
Applications

- Wireless handsets
- PCMCIA cards
- DSP core power
- Hand-held instruments
- Battery-powered systems
- Portable information appliances

Features

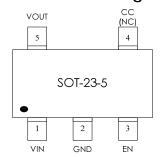
- Miniature SOT-23-5 packages
- 600mA guaranteed output current
- 63μV RMS output voltage noise (10Hz to 100kHz)
 (Vout=3.3V, Cbypass=10nF)
- 580mV typical dropout at 600mA(Vout=3.3V)
- 270mV typical dropout at 300mA(Vout=3.3V)
- 50µA typical quiescent current
- 1nA typical shutdown mode
- Fast line and load transient response
- 140µs typical fast turn-on time (Vout=3.3V, Cbypass=10nF)
- 2.2V to 5.5V input range
- Stable with small ceramic output capacitors
- Over temperature and over current protection
- ±2% output voltage tolerance

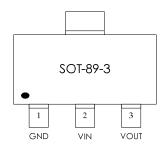
Typical Application

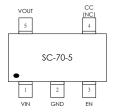


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Connection Diagrams







Order information

EMP8021-XXVF05NRR

XX Output voltage VF05 SOT-23-5 Package

NRR RoHS & Halogen free package

Rating: -40 to 85°C Package in Tape & Reel

EMP8021-XXVG03NRR

XX Output voltage VG03 SOT-89-3 Package

NRR RoHS & Halogen free package

Rating: -40 to 85°C Package in Tape & Reel

EMP8021-XXVI05NRR

XX Output voltage VI05 SC-70-5 Package

NRR RoHS & Halogen free package

Rating: -40 to 85°C Package in Tape & Reel

Order, Marking & Packing Information

Package	Vout	Product ID.	No. of Pin	EN	CC (NC)	Marking	Packing
	1.8	EMP8021-18VF05NRR					
	2.5	EMP8021-25VF05NRR					
SOT-23-5	2.8	EMP8021-28VF05NRR	5	Y	Y	8021 Tracking Code	Tape & Reel 3Kpcs
	3.0	EMP8021-30VF05NRR				PINI DOT 1 2 3	
	3.3	EMP8021-33VF05NRR					
SC-70-5	3.3	EMP8021-33VI05NRR	5	Y	Y		Tape & Reel 3Kpcs
	1.8	EMP8021-18VG03NRR					
SOT-89-3	2.5	EMP8021-25VG03NRR	3	N		8021	Tape & Reel
	2.8	EMP8021-28VG03NRR		NN	Tracking Code PIN1 DOT 1 2 3	1Kpcs	
	3.3	EMP8021-33VG03NRR					

Pin Functions

Name	SOT-23-5/	SOT-89-3	Function
Name	SC-70-5	301-07-3	Tunction
			Supply Voltage Input
VIN	1	2	Require a minimum input capacitor of close to 1µF to ensure stability and
			sufficient decoupling from the ground pin.
GND	2	1	Ground Pin
			Compensation Capacitor
CC (NC)	4	N/A	Connect an optimum 10nF noise bypass capacitor between the CC and
CC (NC) 4	4		the ground pins to reduce noise in VOUT.
		(Note. It can be floated, but don't connect the CC pin to any DC voltage.)	
			Shutdown Input
EN	3	N/A	Set the regulator into the disable mode by pulling the EN pin low. To keep
EIN			the regulator on during normal operation, connect the EN pin to VIN. The EN
			pin must not exceed VIN under all operating conditions.
VOUT	5	3	Output Voltage Feedback

Functional Block Diagram

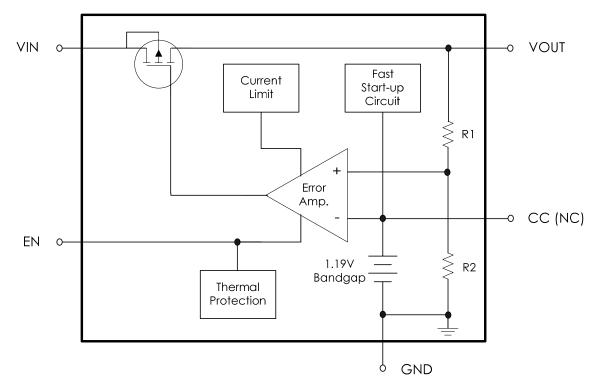


FIG.1. Functional Block Diagram of EMP8021

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Absolute Maximum Ratings (Notes 1, 2)

VIN, VOUT, VEN -0.3V to 6.0V Lead Temperature (Soldering, 10 sec.) 260°C

Power Dissipation (Note 5) ESD Rating

Storage Temperature Range -65°C to 150°C Human Body Model (Note 5) 2KV

Junction Temperature (T_J) 150°C MM 200V

Operating Ratings (Note 1, 2)

Thermal Resistance (θ_{JA}) (Note 3) 135°C /W(SOT-23-5)

Supply Voltage 2.2V to 5.5V 90°C/W (\$OT-89-3)

Storage Temperature Range -40°C to 85°C 331°C/W (SC-70-5)

Thermal Resistance (θ_{JC}) (Note 4) 81°C /W(SOT-23-5)

52°C/W (SOT-89-3)

Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $V_{IN} = V_{OUT} + 1V$ (Note 8), VEN = V_{IN} , $C_{IN} = C_{OUT} = 2.2\mu$ F, $C_{CC} = 33$ nF, $T_A = 25$ °C. **Boldface** limits apply for the operating temperature extremes: -40°C and 85°C.

Symbol	Parameter	Conditions	Min	Typ (Note 6)	Max	Units
V _{IN}	Input Voltage		2.2		5.5	V
	Output Voltage Tolerance	I _{OUT} = 10mA (Note 8)	-2		+2	% of
$\Delta V_{ ext{OTL}}$			-3		+3	Vout (nom)
Іоит	Maximum Output Current	Average DC Current Rating	600			mA
I _{LIMIT}	Output Current Limit		620	700		mA
	Supply Current	I _{OUT} = 0mA		50		μА
ΙQ		I _{OUT} = 600mA		225		
	Shutdown Supply Current	V _{OUT} = 0V, EN = GND		0.001	1	
	Dropout Voltage Iout = 600mA	V _{OUT} = 1.8V		917		
		V _{OUT} = 2.5V		752		
V_{DO}		V _{OUT} = 2.8V		644		mV
		V _{OUT} =3.0V		624		
		V _{OUT} = 3.3V		580		

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Δ V ουτ	Line Regulation	$I_{OUT} = 1 \text{mA}, (V_{OUT} + 1V) \le V_{IN} \le 5.5V$ (Note 9)	-0.1	0.02	0.1	%/V
	Load Regulation	100μA ≤ I _{OUT} ≤ 600mA		0.001		%/mA
		I_{OUT} =10mA,10Hz \leq f \leq 100kHz V_{OUT} = 3.3V,Cbypass = 33nF		63		.,
e _n	Output Voltage Noise	I_{OUT} =10mA,10Hz \leq f \leq 100kHz V_{OUT} = 3.3V,Cbypass = float		205		μV _{RMS}
VEN	EN Input Threshold	V_{IH} , $(V_{OUT} + 1V) \le V_{IN} \le 5.5V$ (Note 8)	1.2			V
VEIN		V_{IL} , $(V_{OUT} + 1V) \le V_{IN} \le 5.5V$ (Note 8)			0.4	V
IEN	EN Input Bias Current	EN = GND or VIN		0.1	100	nA
т	Thermal Shutdown Temperature			167		°C
T _{SD}	Thermal Shutdown Hysteresis			30		C
Тон	Start-Up Time	$C_{OUT} = 10\mu F$, V_{OUT} at 90% of Final Value		140		μs

Note 1: Absolute Maximum ratings indicate limits beyond which damage may occur. Electrical specifications do not apply when operating the device outside of its rated operating conditions.

Note 2: All voltages are with respect to the potential at the ground pin.

Note 3: θ JA is measured in the natural convection at TA=25°C on a high effective thermal conductivity test board (2 layers , 2SOP) of JEDEC 51-7 thermal measurement standard.

Note 4: θ _{JC} represents the resistance to the heat flows the chip to package top case.

Note 5: Maximum Power dissipation for the device is calculated using the following equations:

$$P_D = \frac{T_J(MAX)^{-T}A}{\theta_{JA}}$$

Where T_J (MAX) is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance. E.g. for the SOT-23-5 package $\theta_{JA} = 135^{\circ}$ C/W, T_J (MAX) = 150°C and using $T_A = 25^{\circ}$ C, the maximum power dissipation is found to be 925mW. The derating factor (-1/ θ_{JA}) = -7.4mW/°C, thus below 25°C the power dissipation figure can be increased by 7.4mW per degree, and similarity decreased by this factor for temperatures above 25°C.

Note 6: Typical Values represent the most likely parametric norm.

Note 7: Human body model: $1.5k\Omega$ in series with 100pF.

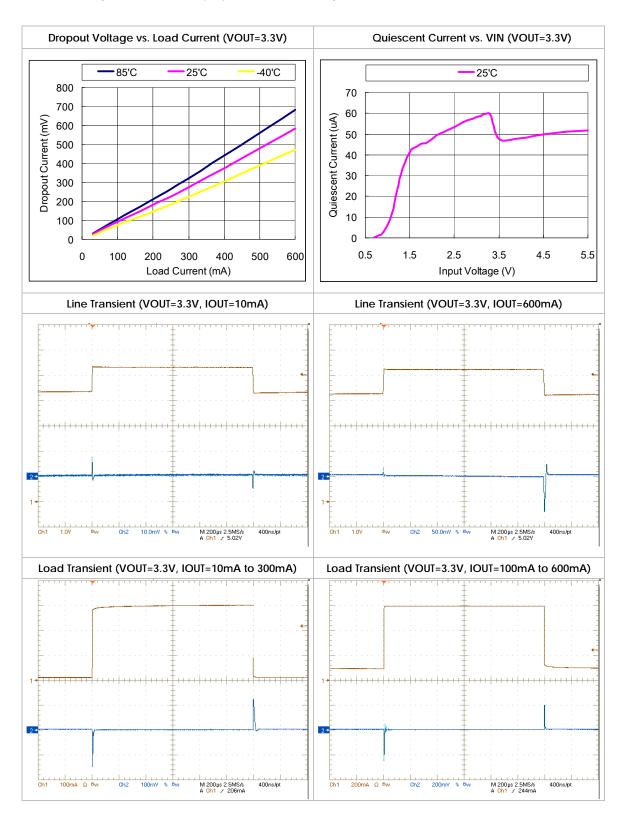
Note 8: Condition does not apply to input voltages below 2.2V since this is the minimum input operating voltage.

Note 9: Dropout voltage is measured by reducing V_{IN} until V_{OUT} drops 100mV from its nominal value. Dropout voltage does not apply to the regulator versions with V_{OUT} less than 1.8V.

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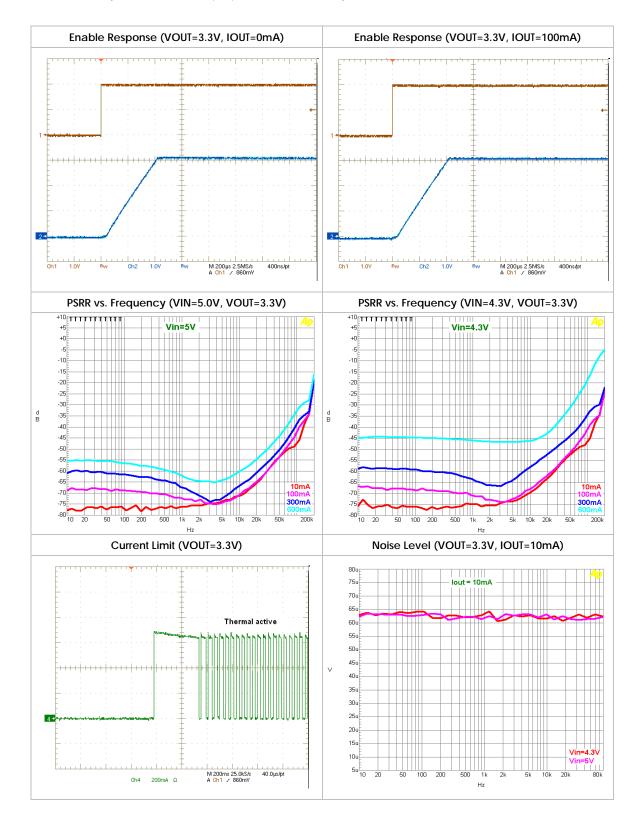
Typical Performance Characteristics

Unless otherwise specified, VIN = $V_{OUT (NOM)}$ + 1V, C_{IN} = C_{OUT} = 2.2 μ F, C_{CC} = 33nF, T_A = 25°C, VEN = VIN.



Typical Performance Characteristics (cont.)

Unless otherwise specified, VIN = $V_{OUT\ (NOM)}$ + 1V, C_{IN} = C_{OUT} = 2.2 μ F, C_{CC} = 33nF, T_A = 25°C, VEN = VIN.



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Application Information

General Description

Referring to Fig.1 as shown in the Functional Block Diagram section, the EMP8021 adopts the classical regulator topology in which negative feedback control is used to perform the desired voltage regulating function. The negative feedback is formed by using feedback resistors (R1, R2) to sample the output voltage for the non-inverting input of the error amplifier, whose inverting input is set to the bandgap reference voltage. By virtue of its high open-loop gain, the error amplifier operates to ensure that the sampled output feedback voltage at its non-inverting input is virtually equal to the preset bandgap reference voltage.

The error amplifier compares the voltage difference at its inputs and produces an appropriate driving voltage to the P-channel MOS pass transistor to control the amount of current reaching the output. If there are changes in the output voltage due to load changes, the feedback resistors register such changes to the non-inverting input of the error amplifier. The error amplifier then adjusts its driving voltage to maintain virtual short between its two input nodes under all loading conditions. In a nutshell, the regulation of the output voltage is achieved as a direct result of the error amplifier keeping its input voltages equal. This negative feedback control topology is further augmented by the shutdown, the fault detection, and the temperature and current protection circuitry.

Output Capacitor

The EMP8021 is specially designed for use with ceramic output capacitors of as low as $2.2\mu F$ to take advantage of the savings in cost and space as well as the superior filtering of high frequency noise. Capacitors of higher value or other types may be used, but it is important to make sure its equivalent series resistance (ESR) be restricted to less than 0.5Ω . The use of larger capacitors with smaller ESR values is desirable for applications involving large and fast input or output transients, as well as for situations where the application systems are not physically located immediately adjacent to the battery power source. Typical ceramic capacitors suitable for use with the EMP8021 are X5R and X7R. The X5R and the X7R capacitors are able to maintain their capacitance values to within $\pm 20\%$ and $\pm 10\%$, respectively, as the temperature increases.

No-Load Stability

The EMP8021 is capable of stable operation during no-load conditions, a mandatory feature for some applications such as CMOS RAM keep-alive operations.

Input Capacitor

A minimum input capacitance of 1µF is required for EMP8021. The capacitor value may be increased without limit. Improper workbench set-ups may have adverse effects on the normal operation of the regulator. A case in point is the instability that may result from long supply lead inductance coupling to the output through the gate capacitance of the pass transistor. This will establish a pseudo LCR network, and is likely to happen under high current conditions or near dropout. A 10µF tantalum input capacitor will dampen the parasitic LCR action thanks to its high ESR. However, cautions should be exercised to avoid regulator short-circuit damage when tantalum capacitors are used, for they are prone to fail in short-circuit operating conditions.

Compensation (Noise Bypass) Capacitor

Substantial reduction in the output voltage noise of the EMP8021 is accomplished through the connection of the noise bypass capacitor CC (10nF optimum) between pin 4 and the ground. Because pin 4 connects directly to the high

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impedance output of the bandgap reference circuit, the level of the DC leakage currents in the CC capacitors used will adversely reduce the regulator output voltage. This sets the DC leakage level as the key selection criterion of the CC capacitor types for use with the EMP8021. NPO and COG ceramic capacitors typically offer very low leakage. Although the use of the CC capacitors does not affect the transient response, it does affect the turn-on time of the regulator. Trade off exists between output noise level and turn-on time when selecting the CC capacitor value.

Power Dissipation and Thermal Shutdown

Thermal overload results from excessive power dissipation that causes the IC junction temperature to increase beyond a safe operating level. The EMP8021 relies on dedicated thermal shutdown circuitry to limit its total power dissipation. An IC junction temperature TJ exceeding 167° C will trigger the thermal shutdown logic, turning off the P-channel MOS pass transistor. The pass transistor turns on again after the junction cools off by about 30°C. When continuous thermal overload conditions persist, this thermal shutdown action then results in a pulsed waveform at the output of the regulator. The concept of thermal resistance $\theta_{\rm JA}$ (°C/W) is often used to describe an IC junction's relative readiness in allowing its thermal energy to dissipate to its ambient air. An IC junction with a low thermal resistance is preferred because it is relatively effective in dissipating its thermal energy to its ambient, thus resulting in a relatively low and desirable junction temperature. The relationship between θ JA and TJ is as follows:

$$T_J = \theta_{JA} (PD) + T_A$$

T_A is the ambient temperature, and P_D is the power generated by the IC and can be written as:

$$P_D = I_{OUT} (V_{IN} - V_{OUT})$$

As the above equations show, it is desirable to work with ICs whose θ_{JA} values are small such that T_J does not increase strongly with P_D . To avoid thermally overloading the EMP8021, refrain from exceeding the absolute maximum junction temperature rating of 150°C under continuous operating conditions. Overstressing the regulator with high loading currents and elevated input-to-output differential voltages can increase the IC die temperature significantly.

Shutdown

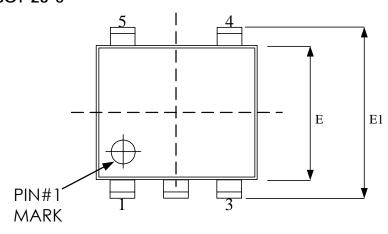
The EMP8021 enters the sleep mode when the EN pin is low. When this occurs, the pass transistor, the error amplifier, and the biasing circuits, including the bandgap reference, are turned off, thus reducing the supply current to typically 1nA. Such a low supply current makes the EMP8021 best suited for battery-powered applications. The maximum guaranteed voltage at the EN pin for the sleep mode to take effect is 0.4V. A minimum guaranteed voltage of 1.2V at the EN pin will activate the EMP8021. Direct connection of the EN pin to the VIN to keep the regulator on is allowed for the EMP8021. In this case, the EN pin must not exceed the supply voltage VIN.

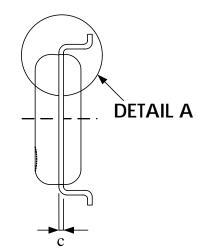
Fast Start-Up

Fast start-up time is important for overall system efficiency improvement. The EMP8021 assures fast start-up speed when using the optional noise bypass capacitor (CC). To shorten start-up time, the EMP8021 internally supplies a current to charge up the capacitor until it reaches about 90% of its final value.

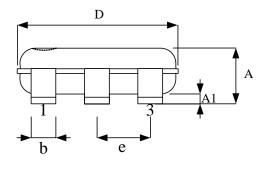
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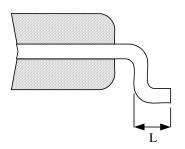
Package Outline Drawing SOT-23-5





TOP VIEW



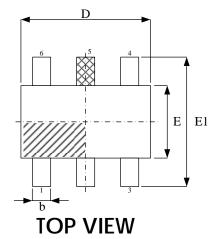


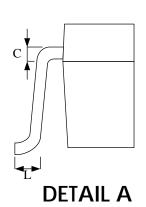
SIDE VIEW

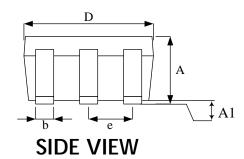
DETAIL A

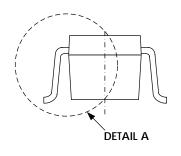
Cyronia ol	Dimension in mm			
Symbol	Min.	Max.		
А	0.90	1.45		
A1	0.00	0.15		
Ъ	0.30	0.50		
С	0.08	0.25		
D	2.70	3.10		
Е	1.40	1.80		
E1	2.60	3.00		
е	0.95	BSC		
L	0.30	0.60		

Package Outline Drawing SC70





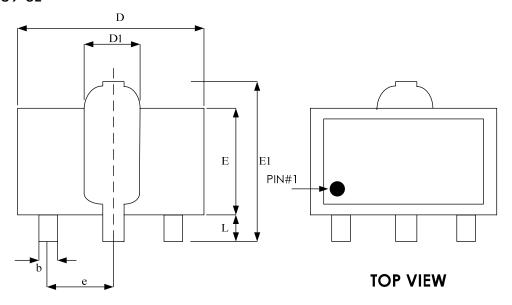




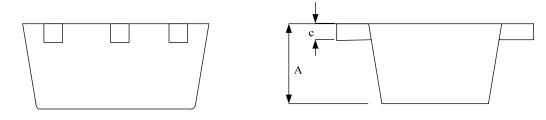
Cymala o 1	Dimension in mm			
Symbol	Min.	Max.		
А	0.80	1.10		
A1	0.00	0.10		
Ъ	0.15	0.30		
С	0.08	0.22		
D	1.85	2.15		
Е	1.10	1.40		
E1	1.80	2.40		
е	0.65	BSC		
L	0.26	0.46		

* This drawing includes SC70 5&6 lead. For 5 lead packages, the No.5 was removed.

Package Outline Drawing SOT-89-3L



BOTTOM VIEW



SIDE VIEW

Cymala ol	Dimension in mm			
Symbol	Min	Max		
А	1.4	1.6		
Ъ	0.4	0.56		
С	0.35	0.41		
D	4.4	4.6		
D1	1.5	1.83		
Е	2.29	2.6		
E1	3.94	4.25		
е	1.50	BSC		
L	0.89	1.2		

Revision History

Revision	Date	Description
0.1	2010.1.13	Original
0.2	2010.08.27	1) Added 2.8V Vout version. 2) Added Dropout voltage for Vout=2.8V 3) Node. 9 item revised. 4) Modified I _{OUT} = 1mA, (V _{OUT} + 0.5V) ≤ V _{IN} ≤ 5.5V →I _{OUT} = 1mA, (V _{OUT} + 1V) ≤ V _{IN} ≤ 5.5V for Electrical Characteristics.
0.3	2011.04.20	Add 3.3V option for SC-70 package
1.0	2011.08.16	Modify output voltage tolerance Add output voltage 1.8V for SOT-23-5 Add output voltage 1.8V and 3.3V for SOT-89-3 Removed "preliminary"
1.1	2011.08.29	 Add output voltage 2.8V for SOT-89-3 Change outline spec
1.2	2012.08.24	 Add output voltage 2.5V \ 3.0V for SOT-23-5 Change outline spec. Updated the package outline drawing.
1.3	2013.10.23	Modify package outline drawing

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